

MOSFETs   Silicon N-Channel MOS (DTMOSVI)

TK125N60Z1

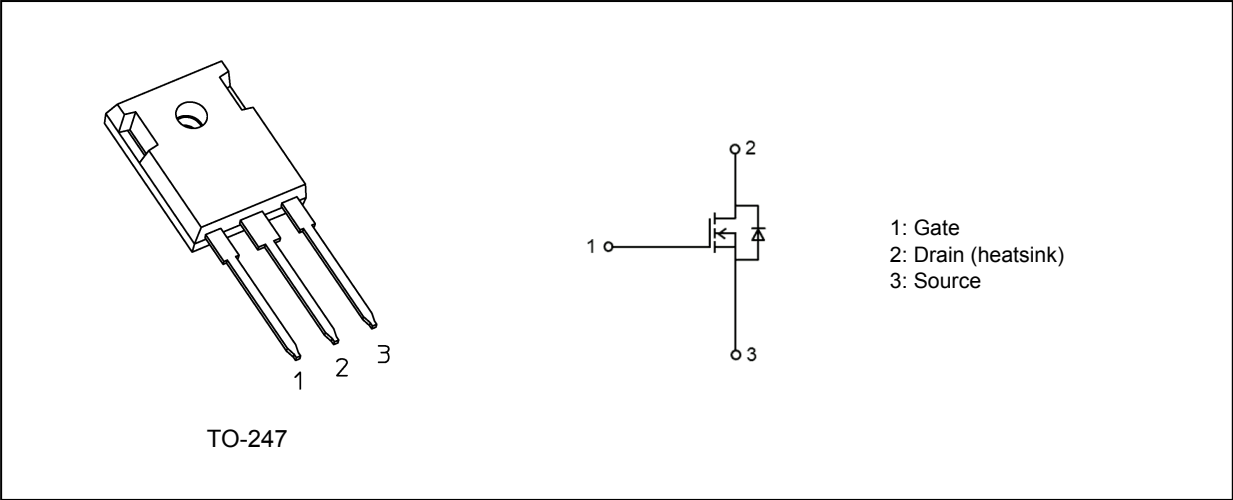
1. Applications

- Switching Power Supplies

2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.105 \, \Omega$  (typ.)
- (2) High-speed switching properties with lower capacitance.
- (3) Enhancement mode:  $V_{th} = 3 \text{ to } 4 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 0.73 \text{ mA}$ )

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ( $T_a = 25 \, ^\circ\text{C}$  unless otherwise specified)

| Characteristics                                    | Symbol    | Rating     | Unit             |
|--|-----------|------------|------------------|
| Drain-source voltage                               | $V_{DSS}$ | 600        | V                |
| Gate-source voltage                                | $V_{GSS}$ | $\pm 30$   |                  |
| Drain current (DC) (Note 1)                        | $I_D$     | 20         | A                |
| Drain current (pulsed) (Note 1)                    | $I_{DP}$  | 80         |                  |
| Power dissipation ( $T_c = 25 \, ^\circ\text{C}$ ) | $P_D$     | 150        | W                |
| Single-pulse avalanche energy (Note 2)             | $E_{AS}$  | 242        | mJ               |
| Single-pulse avalanche current                     | $I_{AS}$  | 4.2        |                  |
| Reverse drain current (DC) (Note 1)                | $I_{DR}$  | 20         |                  |
| Reverse drain current (pulsed) (Note 1)            | $I_{DRP}$ | 80         |                  |
| Channel temperature                                | $T_{ch}$  | 150        | $^\circ\text{C}$ |
| Storage temperature                                | $T_{stg}$ | -55 to 150 |                  |
| Mounting torque                                    | TOR       | 0.8        | N · m            |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production  
2024-06

## 5. Thermal Characteristics

| Characteristics                       | Symbol         | Max   | Unit |
|---------------------------------------|----------------|-------|------|
| Channel-to-case thermal resistance    | $R_{th(ch-c)}$ | 0.833 | °C/W |
| Channel-to-ambient thermal resistance | $R_{th(ch-a)}$ | 50    |      |

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2:  $V_{DD} = 90$  V,  $T_{ch} = 25$  °C (initial),  $L = 24.3$  mH,  $I_{AS} = 4.2$  A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

## 6. Electrical Characteristics

### 6.1. Static Characteristics ( $T_a = 25$ °C unless otherwise specified)

| Characteristics                | Symbol        | Test Condition                      | Min | Typ.  | Max     | Unit     |
|--------------------------------|---------------|-------------------------------------|-----|-------|---------|----------|
| Gate leakage current           | $I_{GSS}$     | $V_{GS} = \pm 30$ V, $V_{DS} = 0$ V | —   | —     | $\pm 1$ | $\mu$ A  |
| Drain cut-off current          | $I_{DSS}$     | $V_{DS} = 600$ V, $V_{GS} = 0$ V    | —   | —     | 2       |          |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $I_D = 10$ mA, $V_{GS} = 0$ V       | 600 | —     | —       | V        |
| Gate threshold voltage         | $V_{th}$      | $V_{DS} = 10$ V, $I_D = 0.73$ mA    | 3   | —     | 4       |          |
| Drain-source on-resistance     | $R_{DS(ON)}$  | $V_{GS} = 10$ V, $I_D = 6$ A        | —   | 0.105 | 0.125   | $\Omega$ |

### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

| Characteristics   | Symbol      | Test Condition                                  | Min | Typ. | Max | Unit     |
|---|-------------|---|-----|------|-----|----------|
| Input capacitance   | $C_{iss}$   | $V_{DS} = 300$ V, $V_{GS} = 0$ V, $f = 100$ kHz | —   | 1620 | —   | pF       |
| Reverse transfer capacitance                              | $C_{rss}$   |   | —   | 2.3  | —   |          |
| Output capacitance  | $C_{oss}$   |   | —   | 40   | —   |          |
| Effective output capacitance (Note 3)<br>(energy related) | $C_{O(er)}$ | $V_{DS} = 0$ to 400 V, $V_{GS} = 0$ V           | —   | 70   | —   | pF       |
| Effective output capacitance (Note 4)<br>(time related)   | $C_{O(tr)}$ | $V_{DS} = 0$ to 400 V, $V_{GS} = 0$ V           | —   | 480  | —   |          |
| Gate resistance   | $r_g$       | $V_{DS} = \text{OPEN}$ , $f = 1$ MHz            | —   | 3.2  | —   | $\Omega$ |
| Switching time (rise time)                                | $t_r$       | See Fig. 6.2.1                                  | —   | 32   | —   | ns       |
| Switching time (turn-on time)                             | $t_{on}$    |   | —   | 55   | —   |          |
| Switching time (fall time)                                | $t_f$       |   | —   | 5    | —   |          |
| Switching time (turn-off time)                            | $t_{off}$   |   | —   | 75   | —   | ns       |
| MOSFET dv/dt ruggedness                                   | dv/dt       | $V_{DS} \leq V_{DSS}$ , $I_D \leq 10$ A         | 70  | —    | —   | V/ns     |

Note 3:  $C_{O(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 V to 400 V.

Note 4:  $C_{O(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 V to 400 V.

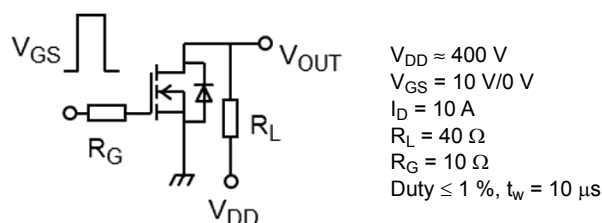


Fig. 6.2.1 Switching Time Test Circuit

## 6.3. Gate Charge Characteristics ( $T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

| Characteristics                                 | Symbol    | Test Condition   | Min | Typ. | Max | Unit |
|---|-----------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | $Q_g$     | $V_{DD} \approx 400\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$ | —   | 28   | —   | nC   |
| Gate-source charge 1                            | $Q_{gs1}$ |  | —   | 9    | —   |      |
| Gate-drain charge                               | $Q_{gd}$  |  | —   | 8    | —   |      |

## 6.4. Source-Drain Characteristics ( $T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

| Characteristics               | Symbol    | Test Condition  | Min | Typ. | Max  | Unit          |
|-------------------------------|-----------|---|-----|------|------|---------------|
| Diode forward voltage         | $V_{DSF}$ | $I_{DR} = 20\text{ A}$ , $V_{GS} = 0\text{ V}$  | —   | —    | -1.7 | V             |
| Reverse recovery time         | $t_{rr}$  | $V_{DD} = 400\text{ V}$ ,<br>$I_{DR} = 10\text{ A}$ , $V_{GS} = 0\text{ V}$<br>$-dI_{DR}/dt = 100\text{ A}/\mu\text{s}$ | —   | 285  | —    | ns            |
| Reverse recovery charge       | $Q_{rr}$  |   | —   | 3.1  | —    | $\mu\text{C}$ |
| Peak reverse recovery current | $I_{rr}$  |   | —   | 22   | —    | A             |
| Diode dv/dt ruggedness        | dv/dt     | $V_{DD} \leq 400\text{ V}$ , $I_{DR} \leq 10\text{ A}$ , $V_{GS} = 0\text{ V}$  | 40  | —    | —    | V/ns          |

## 7. Marking (Note)

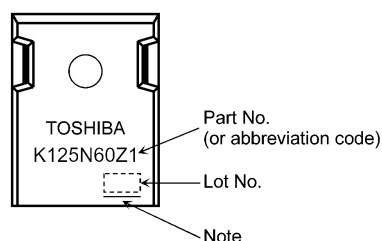


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined:  $[[Pb]]/INCLUDES > MCV$

Underlined:  $[[G]]/RoHS\ COMPATIBLE$  or  $[[G]]/RoHS\ [[Pb]]$

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

## 8. Characteristics Curves (Note)

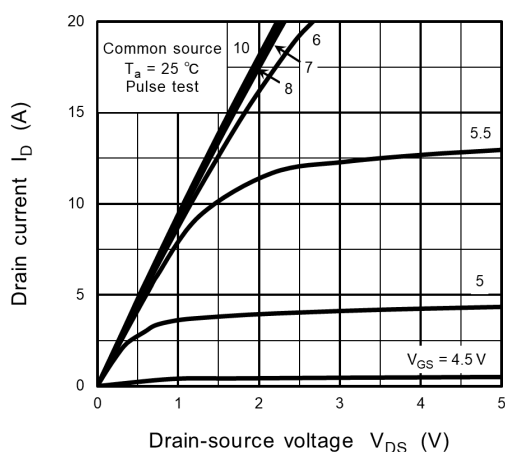


Fig. 8.1  $I_D - V_{DS}$

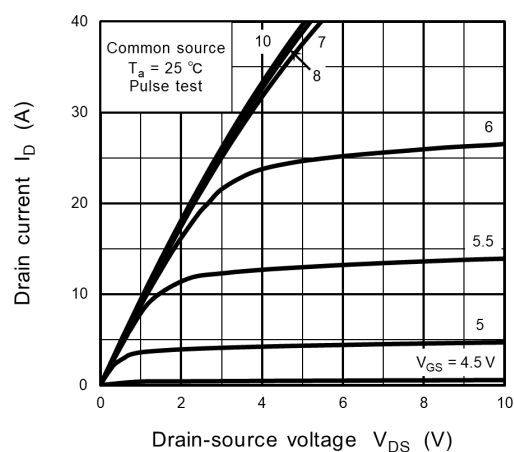


Fig. 8.2  $I_D - V_{DS}$

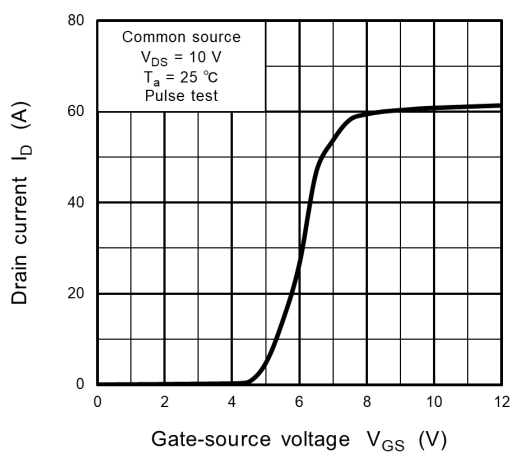


Fig. 8.3  $I_D - V_{GS}$

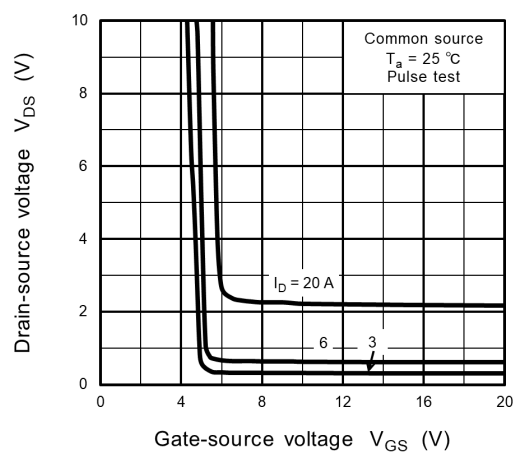


Fig. 8.4  $V_{DS} - V_{GS}$

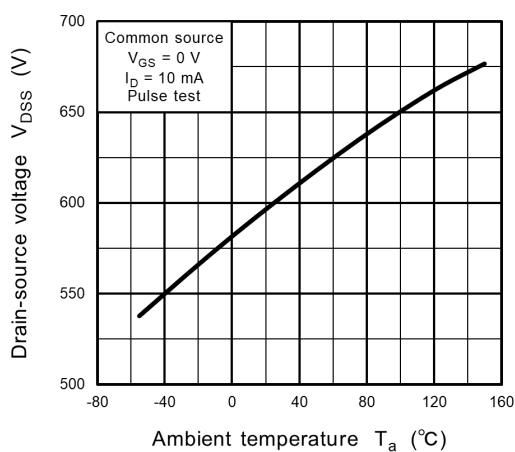


Fig. 8.5  $V_{DS} - T_a$

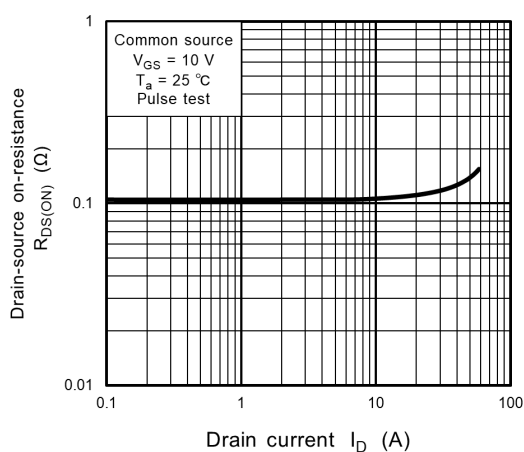


Fig. 8.6  $R_{DS(ON)} - I_D$

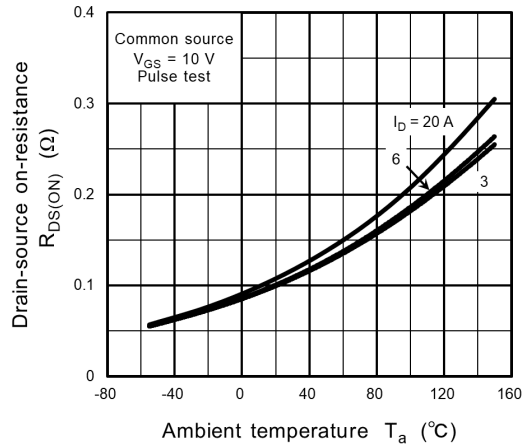


Fig. 8.7  $R_{DS(ON)} - T_a$

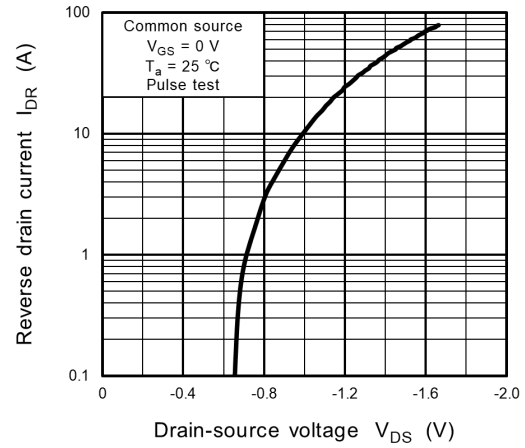


Fig. 8.8  $I_{DR} - V_{DS}$

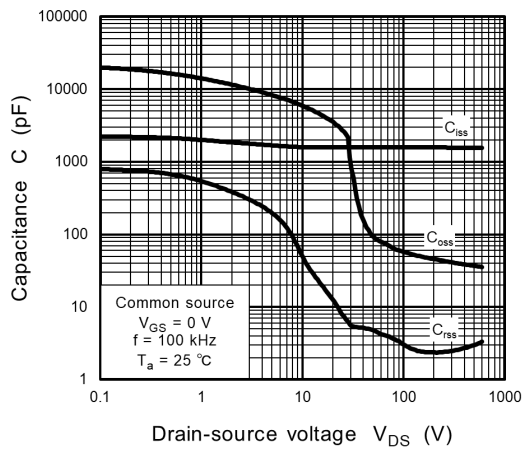


Fig. 8.9  $C - V_{DS}$

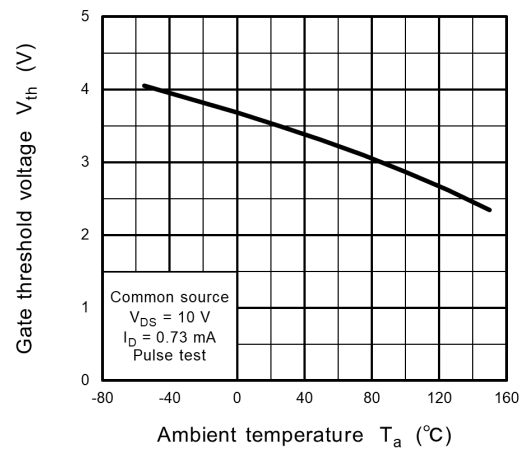


Fig. 8.10  $V_{th} - T_a$

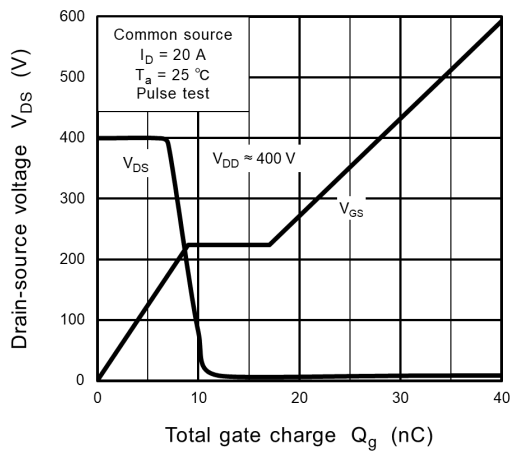


Fig. 8.11 Dynamic Input/Output Characteristics

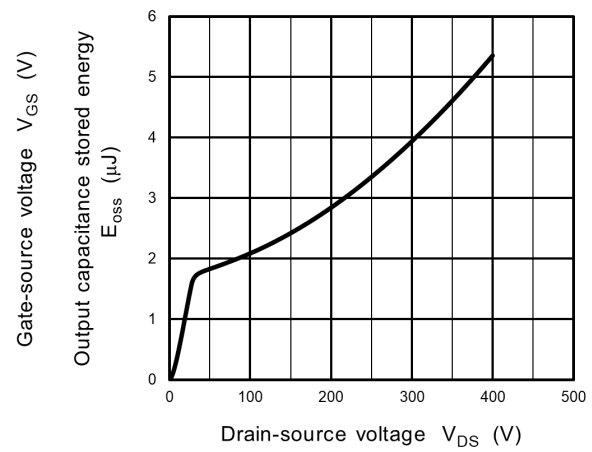


Fig. 8.12  $E_{oss} - V_{DS}$

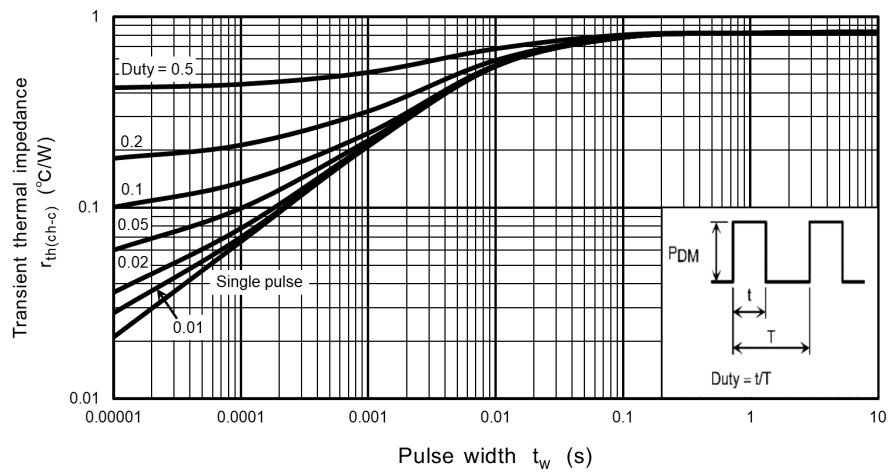


Fig. 8.13  $r_{th} - t_w$   
(Guaranteed Maximum)

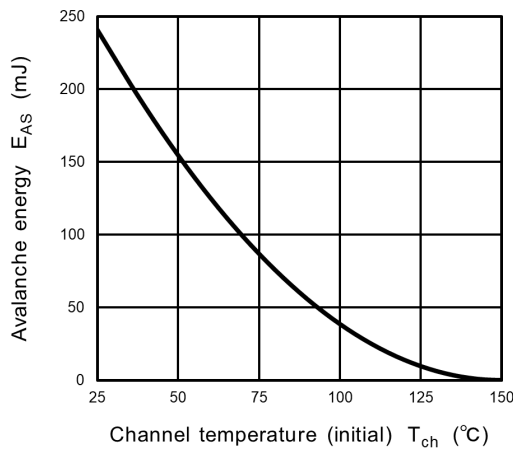


Fig. 8.14  $E_{AS} - T_{ch}$   
(Guaranteed Maximum)

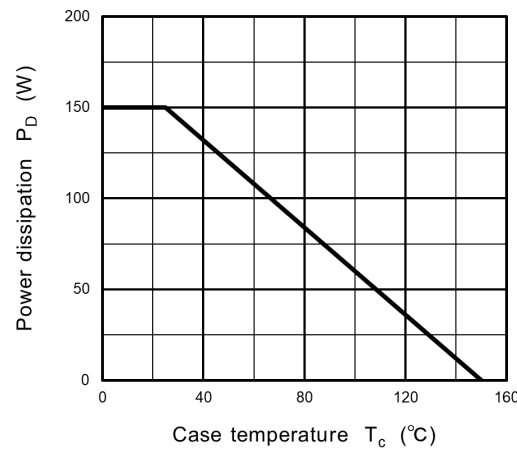


Fig. 8.15  $P_D - T_c$   
(Guaranteed Maximum)

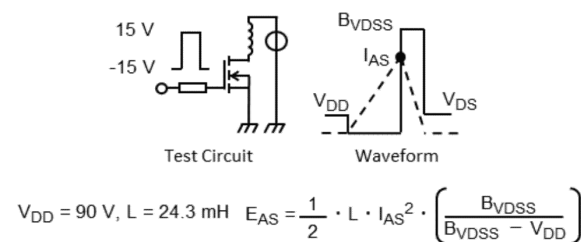


Fig. 8.16 Test Circuit/Waveform

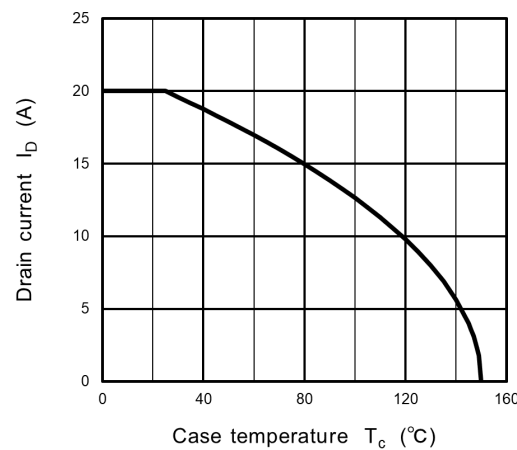
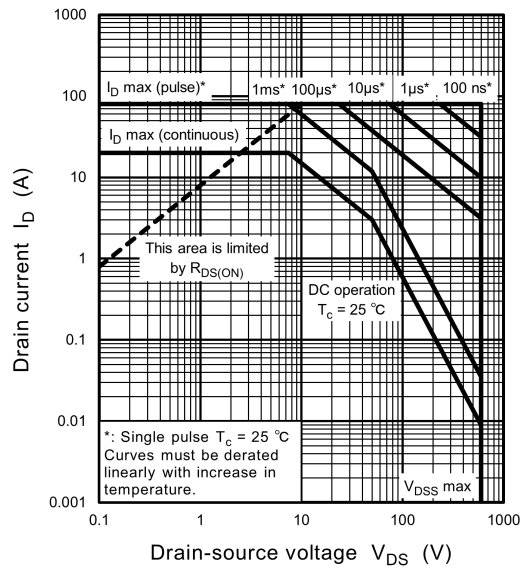


Fig. 8.17  $I_D - T_c$   
(Guaranteed Maximum)

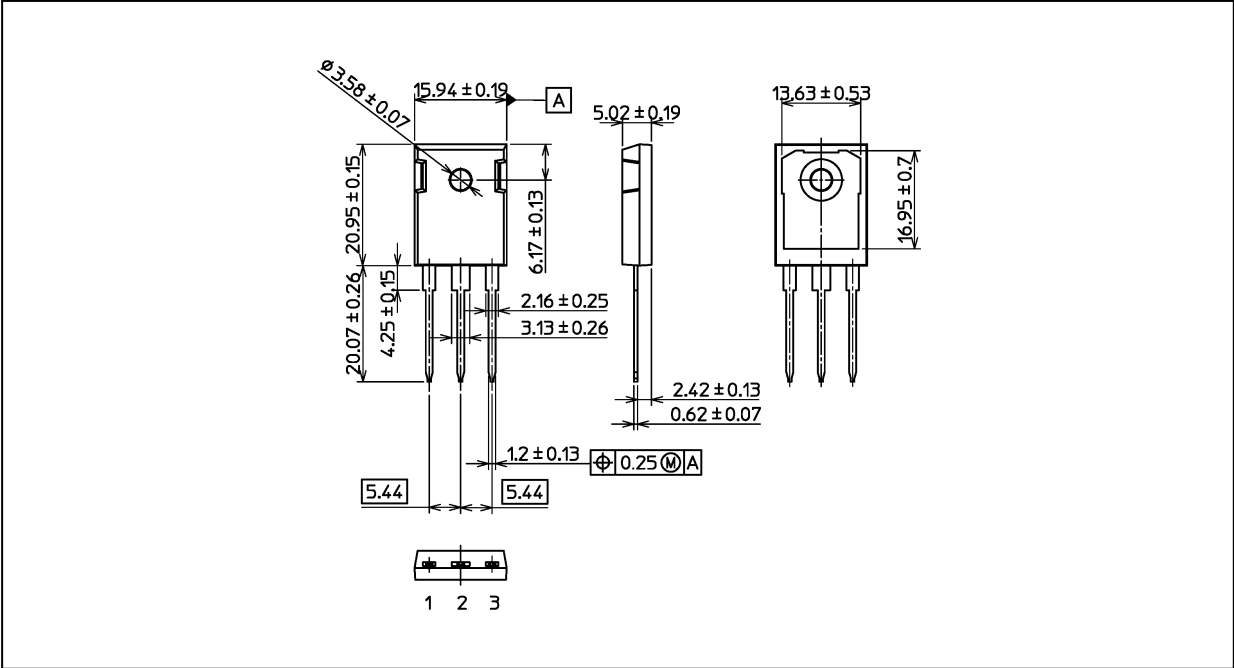


**Fig. 8.18 Safe Operating Area  
(Guaranteed Maximum)**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

| Package Name(s)  |
|------------------|
| TOSHIBA: 2-16L1A |
| Nickname: TO-247 |



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